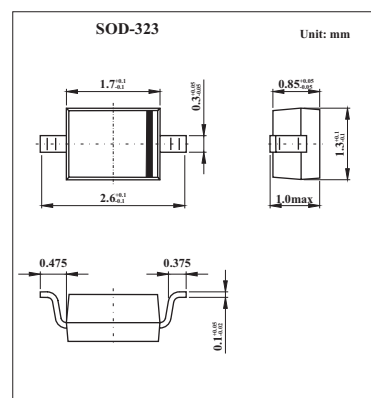


Silicon Schottky diode

BAT15-03W

■ Features

- DBC mixer applications to 12 GHz
- Low noise figure
- Low barrier type

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Value | Unit |
|--|------------|-------------|------|
| Diode reverse voltage | V_R | 4 | V |
| Forward current | I_F | 100 | mA |
| Total power dissipation $T_s = 70^\circ\text{C}$ | P_{tot} | 100 | mW |
| Operating temperature range | T_{op} | -55 to +150 | °C |
| Storage temperature | T_{stg} | -55 to +150 | |
| Junction ambient ⁽¹⁾ | R_{thJA} | ≤ 770 | K/W |
| Junction-soldering point | R_{thJS} | ≤ 690 | K/W |

Note:

1. Package mounted on an epoxy pcb 40 mm × 40 mm × 15 mm/1cm² Cu.

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Min | Typ | Max | Unit |
|--|------------|-----|--------------|--------------|----------|
| Breakdown Voltage $I_{(BR)} = 5\mu\text{A}$ | $V_{(BR)}$ | 4 | | | V |
| Forward voltage $I_F = 1\text{ mA}$ $I_F = 10\text{ mA}$ | V_F | | 0.23 0.32 | 0.32 0.41 | V |
| Diode capacitance $V_R = 0; f = 1\text{ MHz}$ | C_T | | | 0.35 | pF |
| Differential forward resistance $I_F = 10\text{ mA}/50\text{ mA}$ | R_F | | 5.5 | | Ω |

■ Marking

| | |
|---------|---|
| Marking | P |
|---------|---|